

FIG. 11

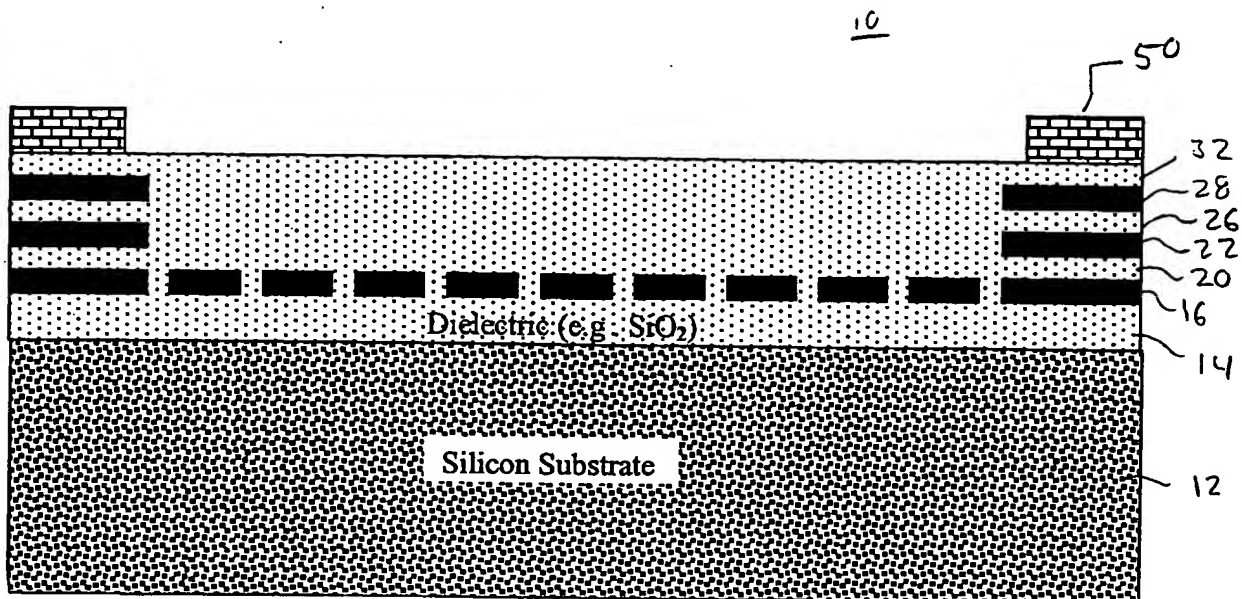


FIG. 12

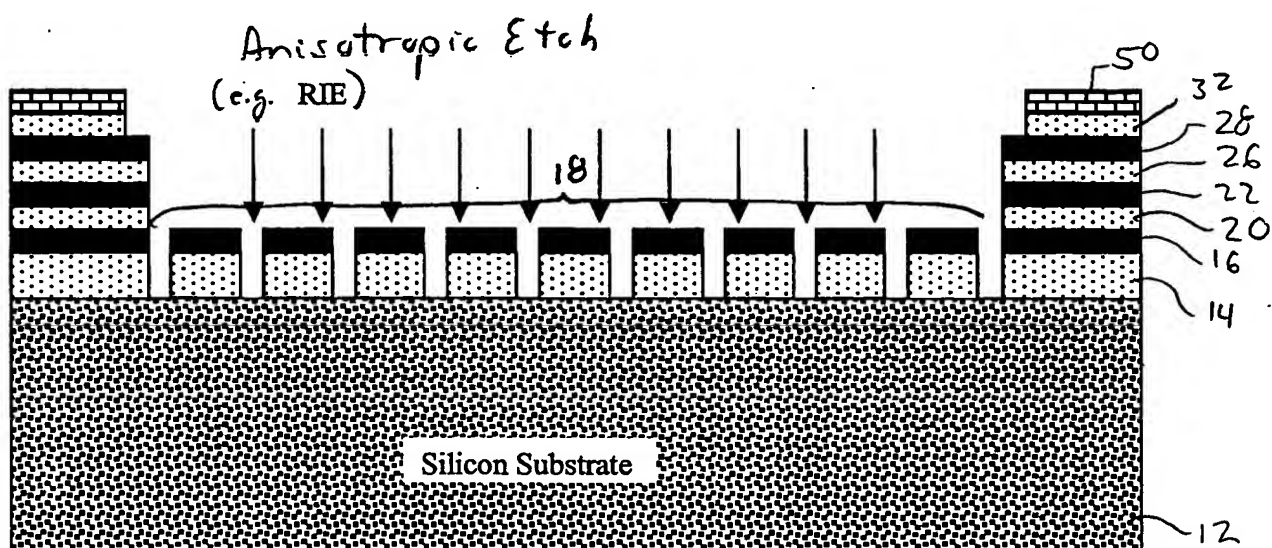


FIG. 13

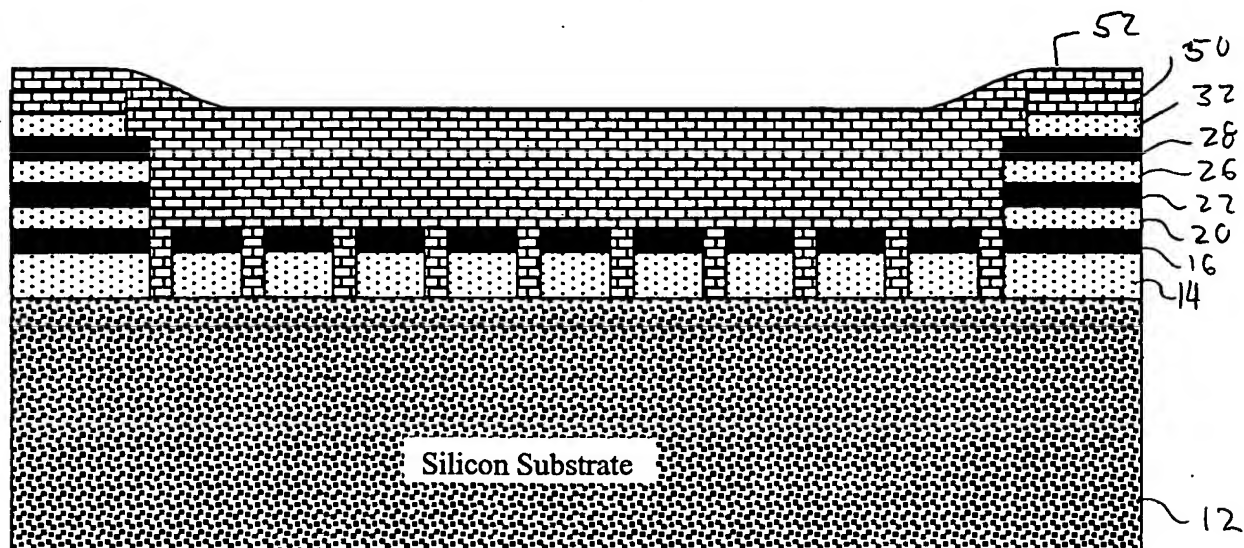


FIG. 14

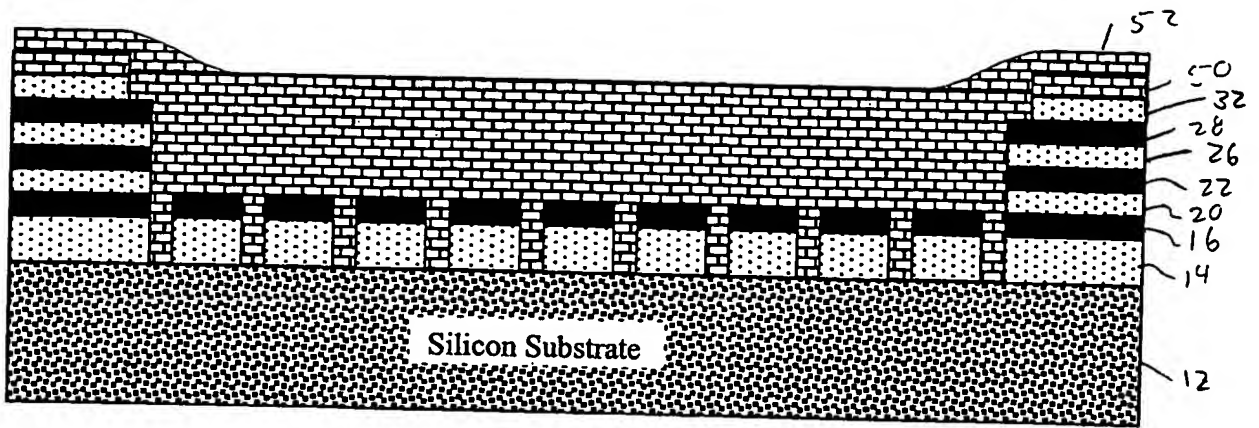


FIG. 15

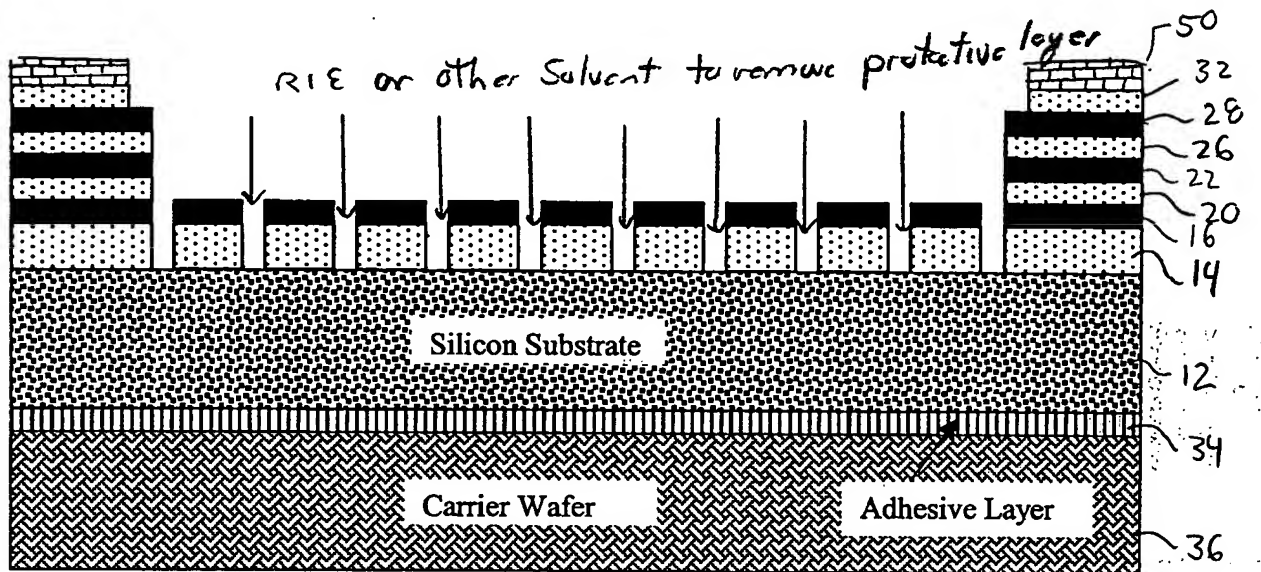




FIG.  
16.

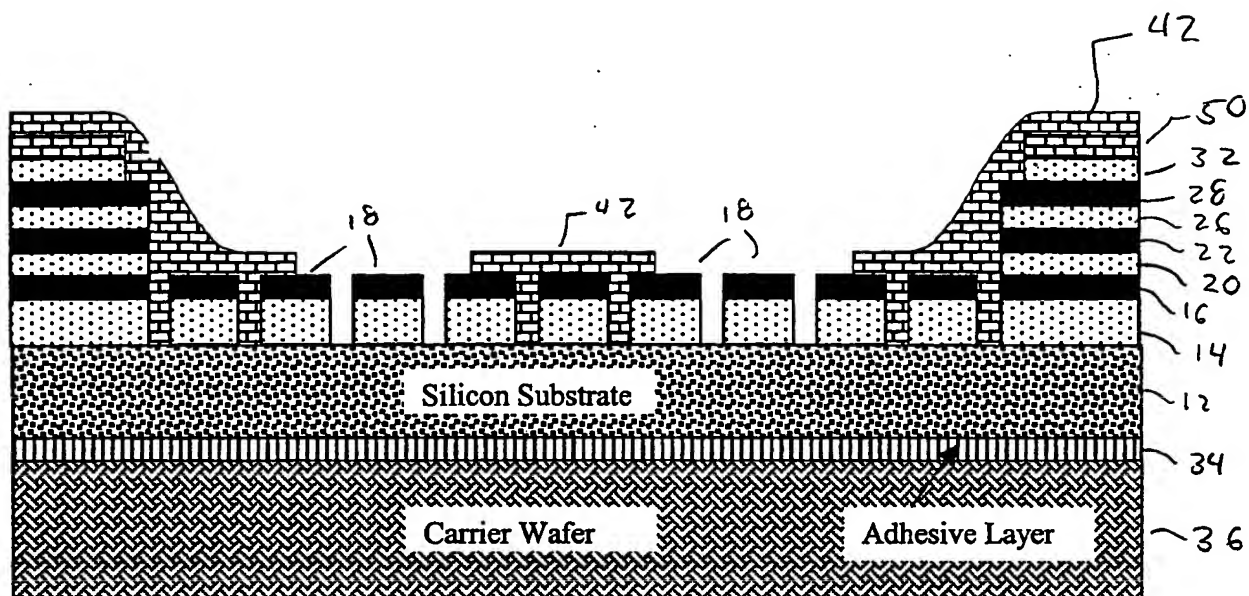


FIG.  
17

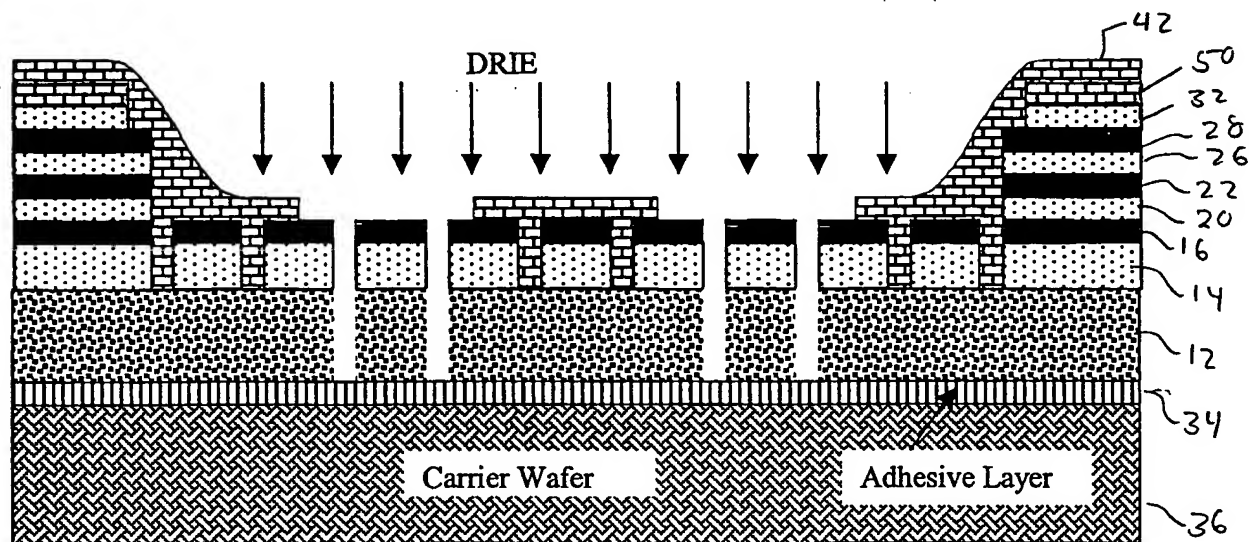


FIG. 18

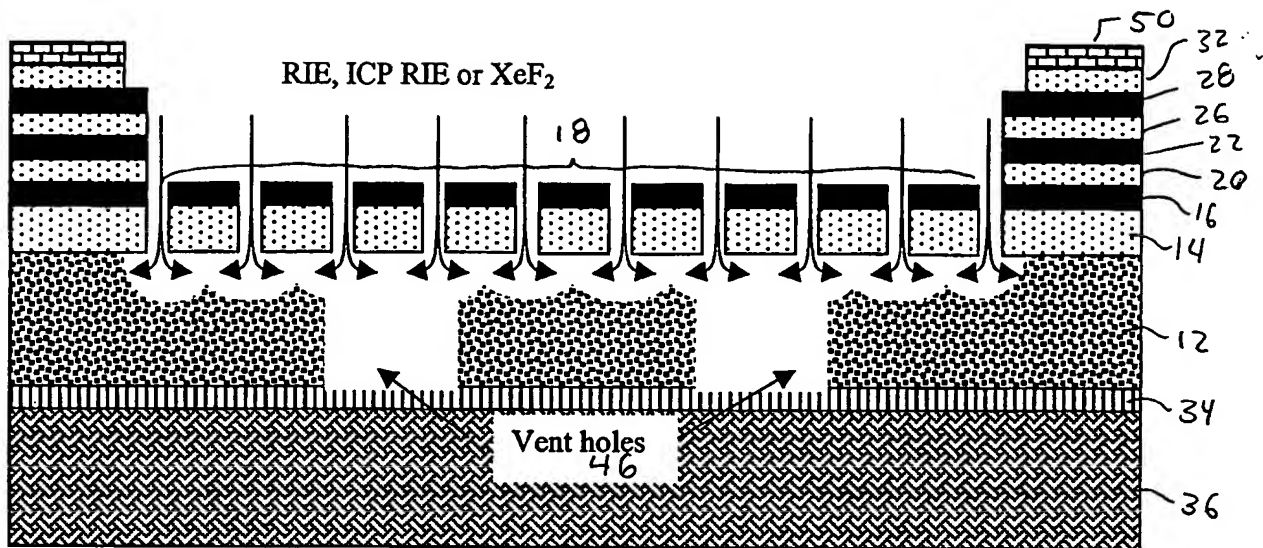


FIG. 19

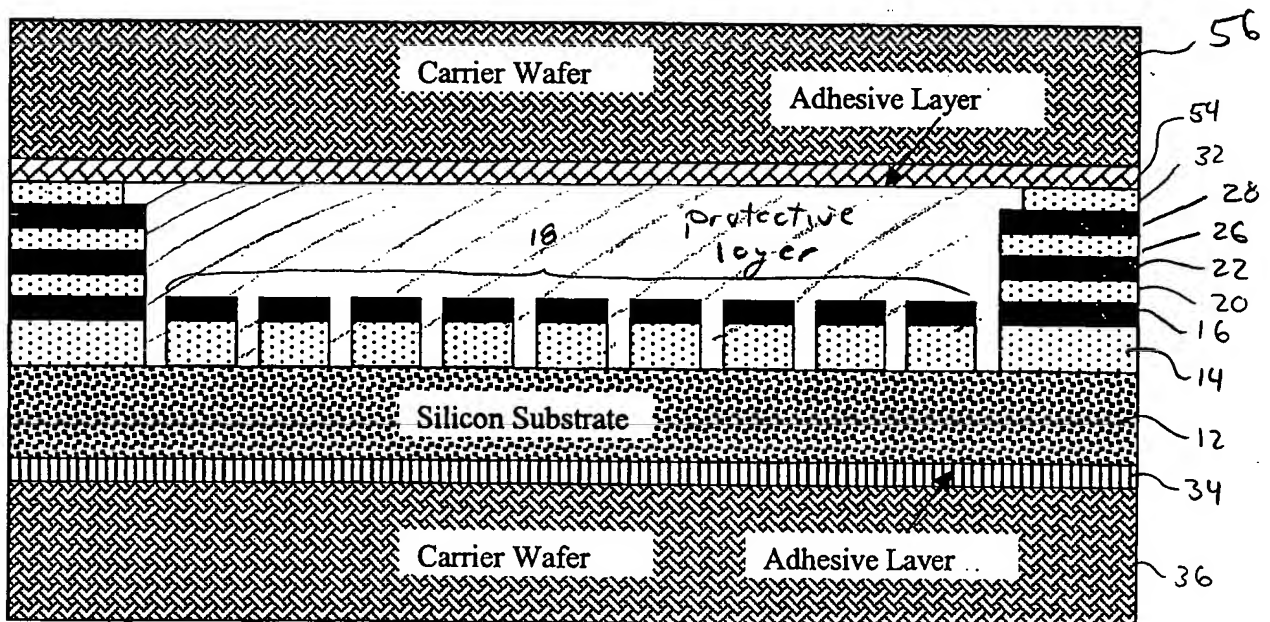




FIG. 20

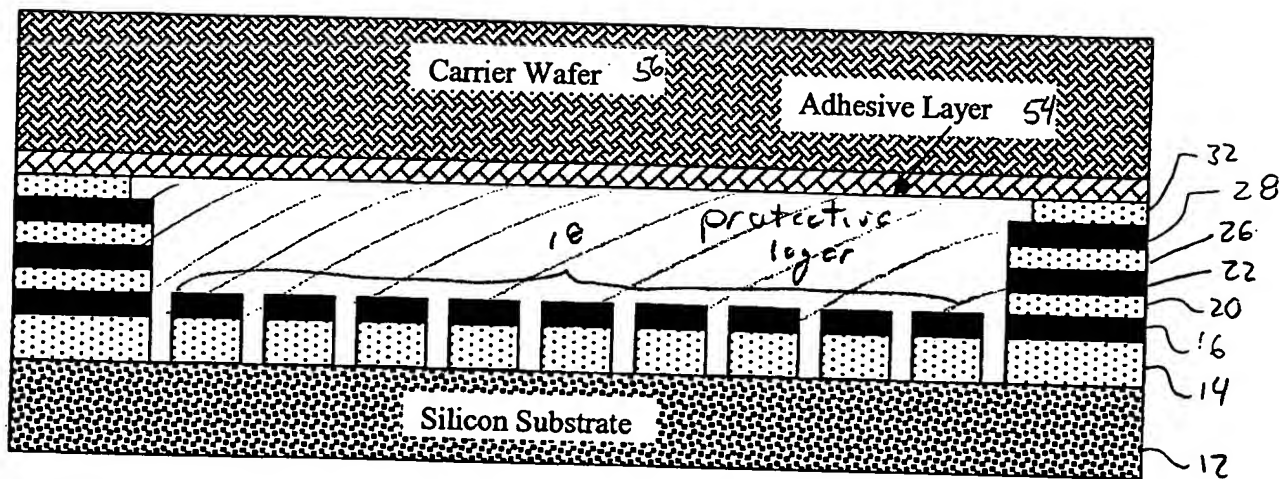


FIG. 21

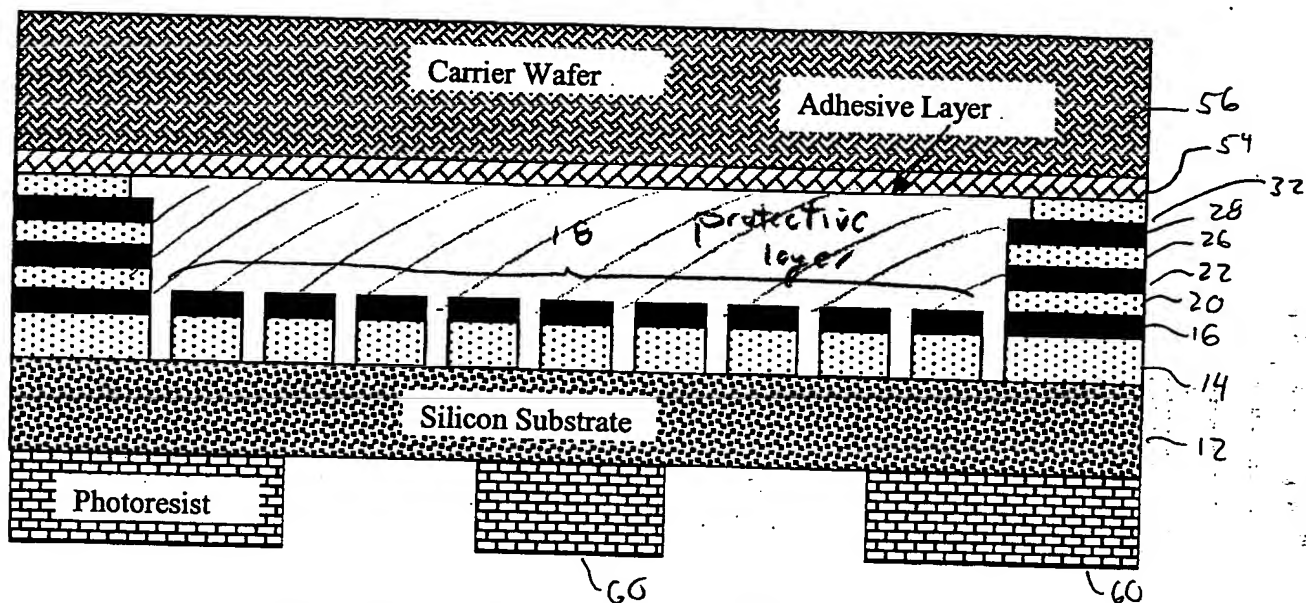


FIG. 22

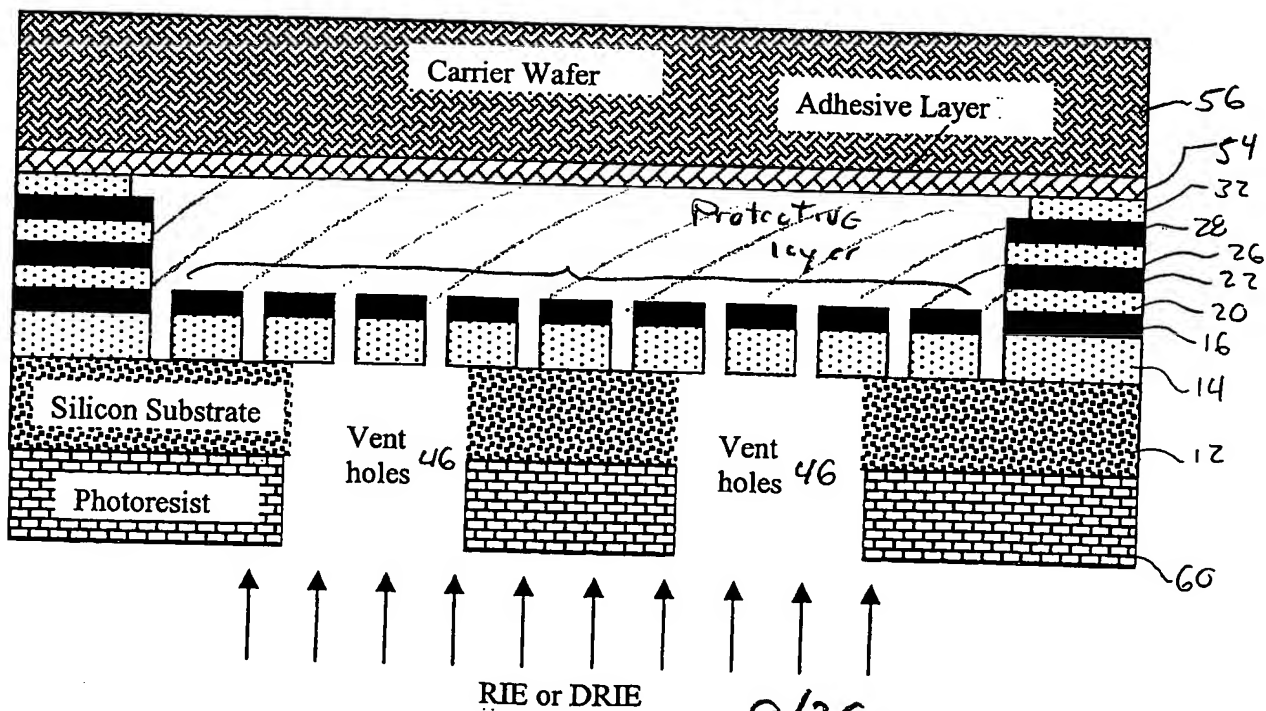


FIG. 23

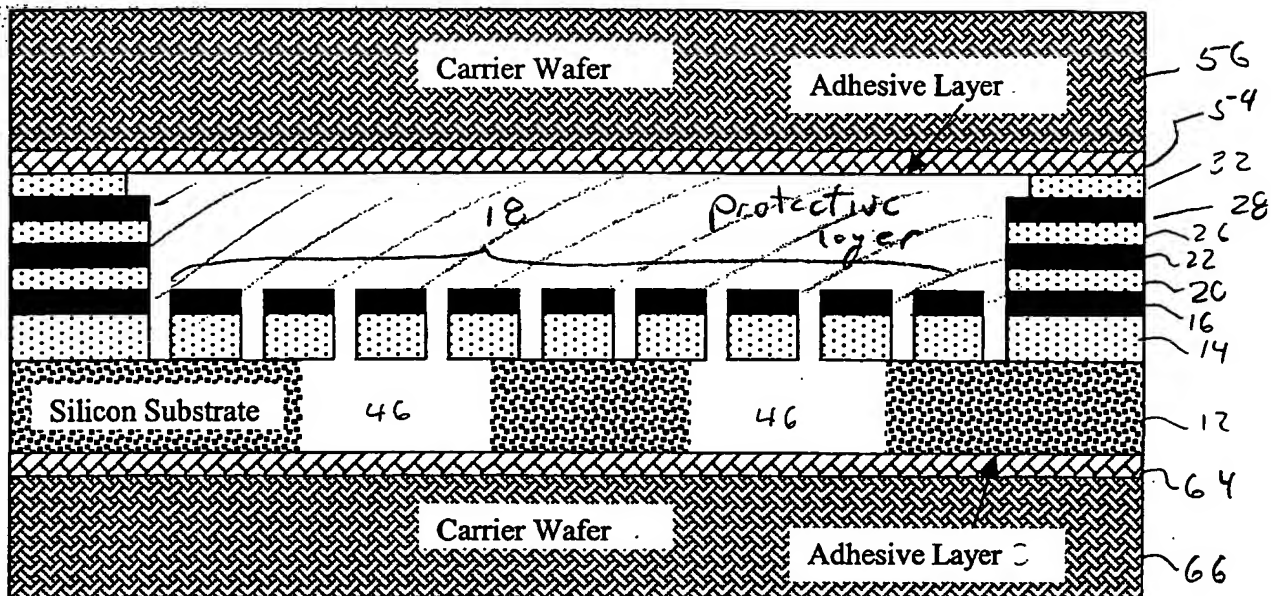


FIG. 24

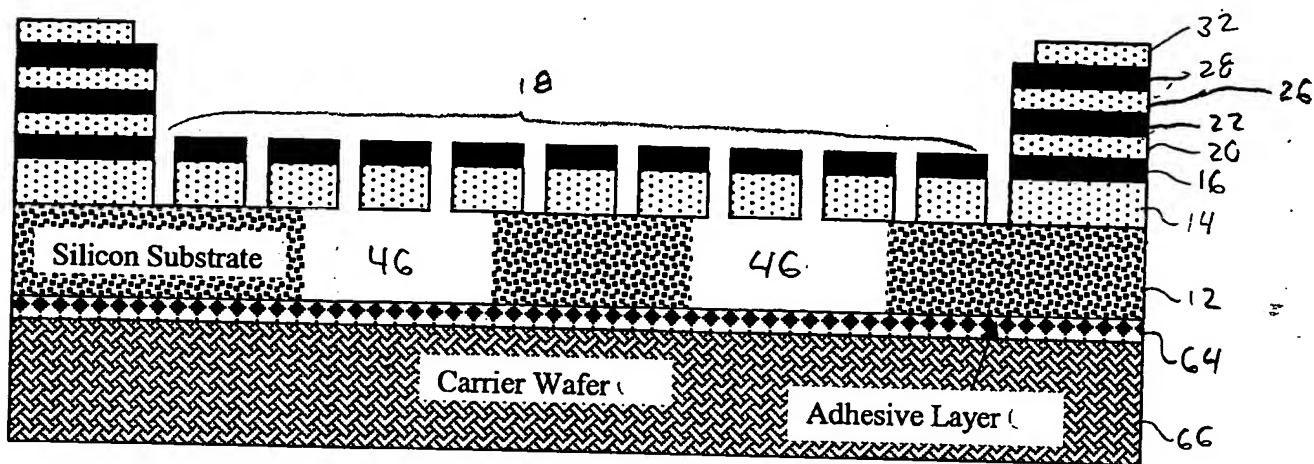


FIG. 25

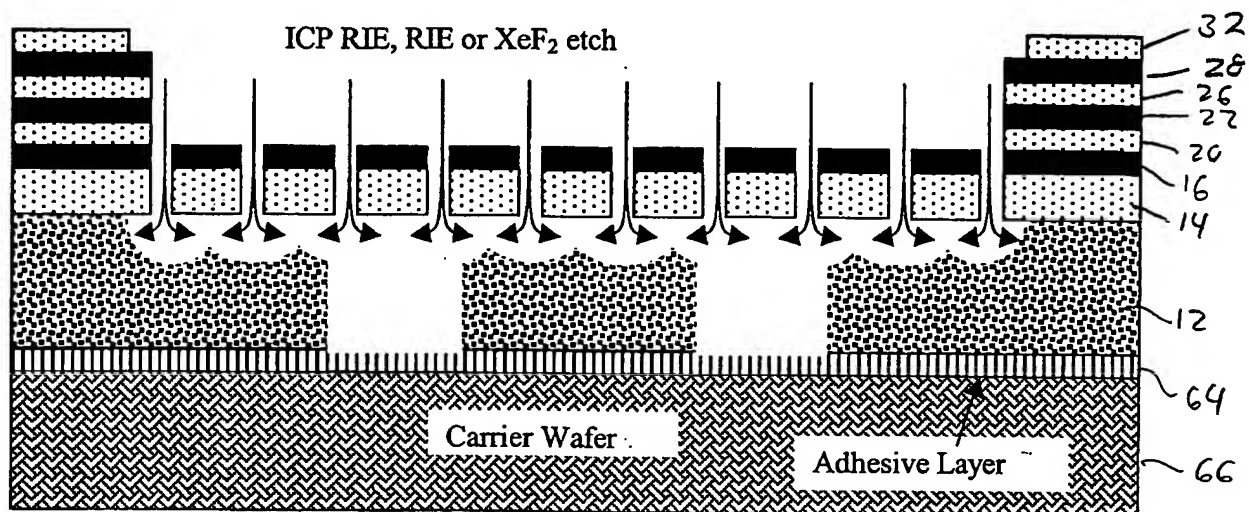


Diagram 10 is a cross-sectional view of a semiconductor device structure. It shows a carrier wafer 36 with an adhesive layer 34 on top. A silicon substrate 12 is bonded to the adhesive layer. A layer 14 is on top of the silicon substrate. A series of openings 18 are formed in layer 14, with arrows indicating etching from the top surface. The openings are filled with a material 16. A layer 20 is on top of the openings, and a layer 22 is on top of layer 20. A layer 26 is on top of layer 22. A layer 32 is on top of layer 26. The top surface is labeled "ICP RIE, RIE or XeF<sub>2</sub> etch".

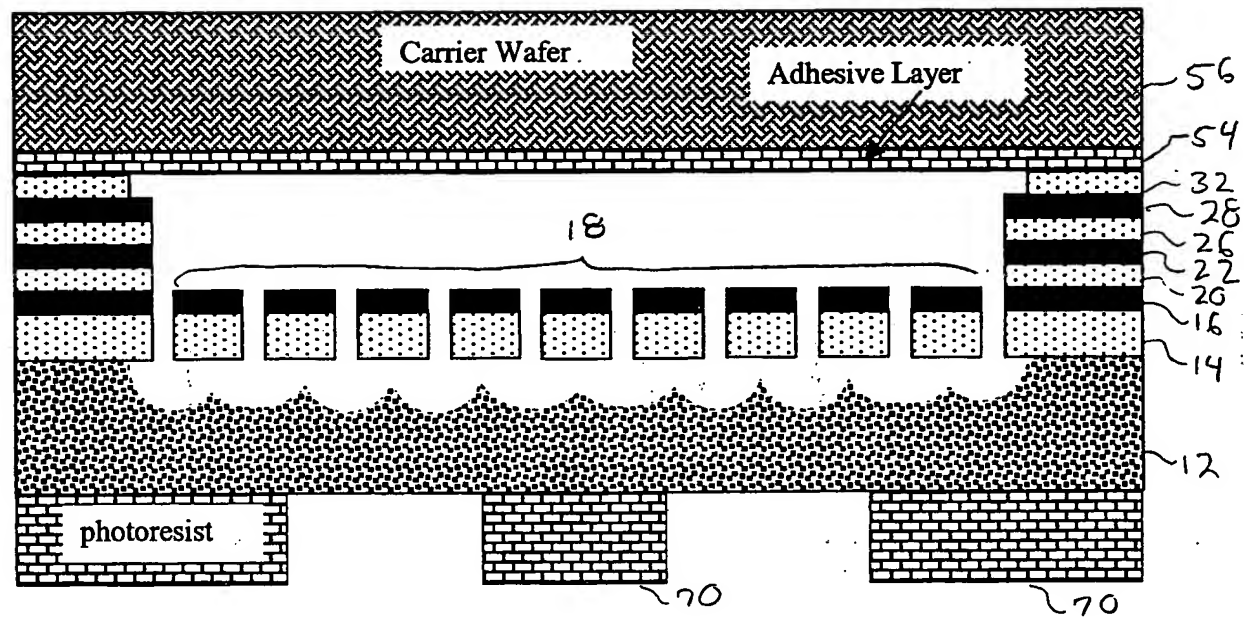
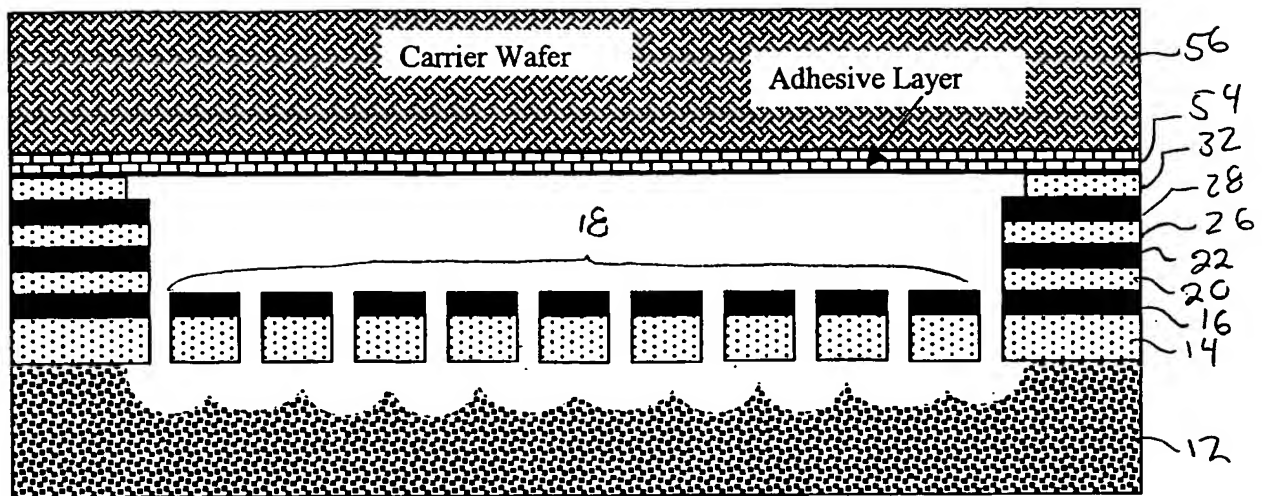


FIG. 30

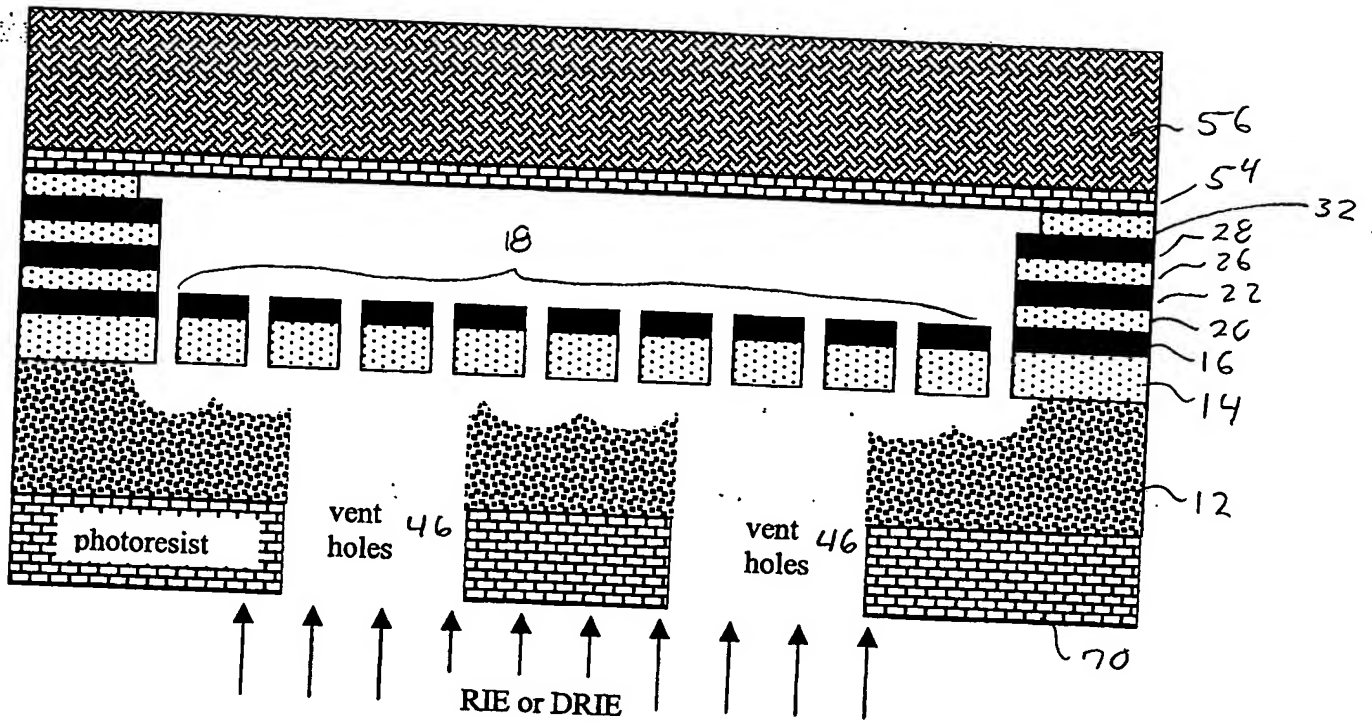


FIG. 31

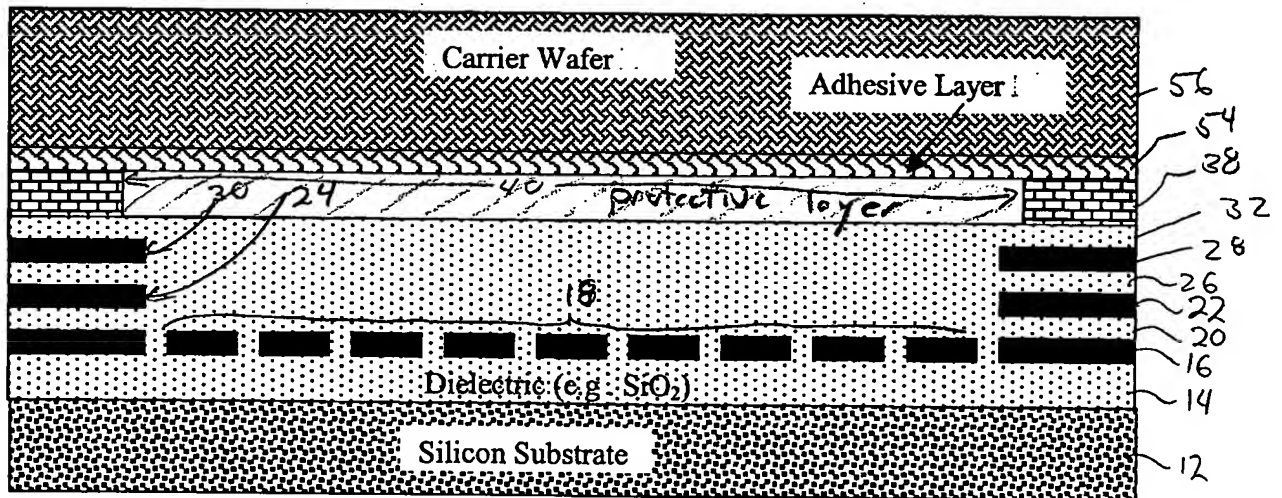




FIG.  
32

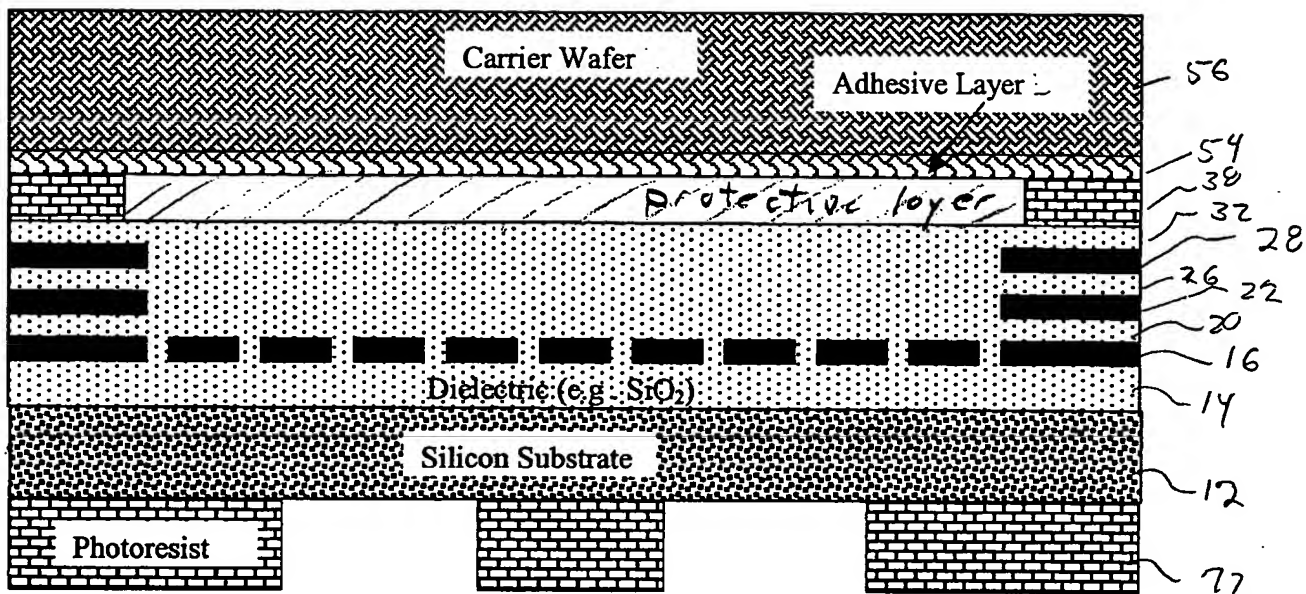


FIG.  
33

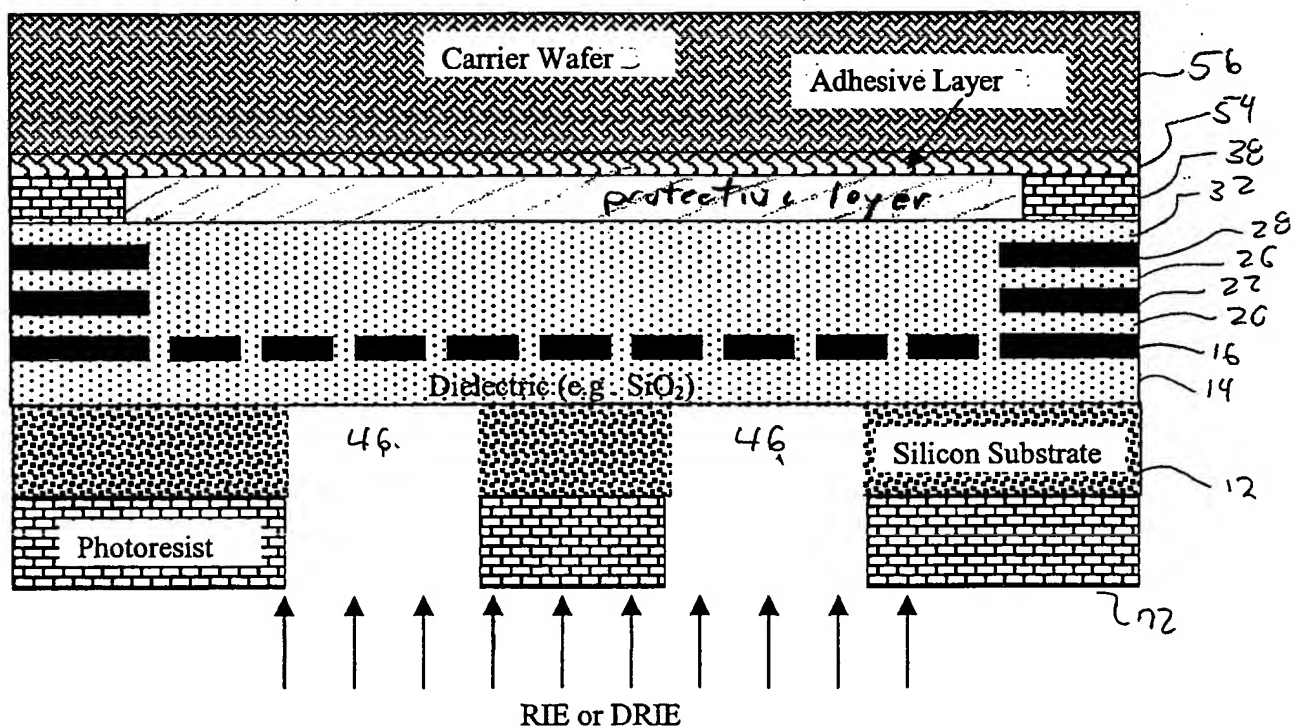




FIG.  
34

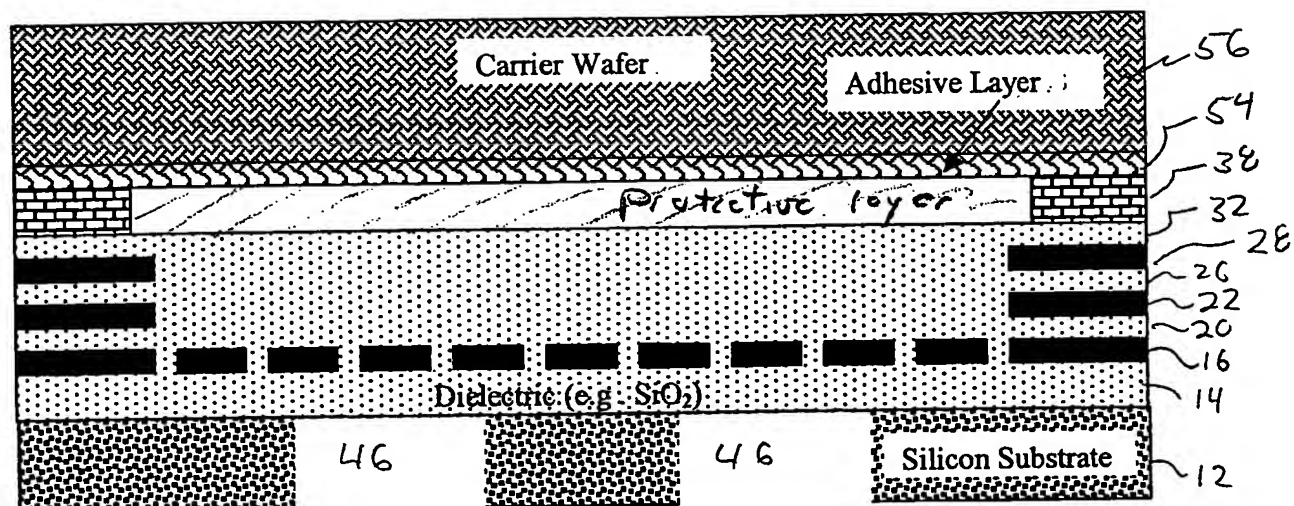


FIG.  
35

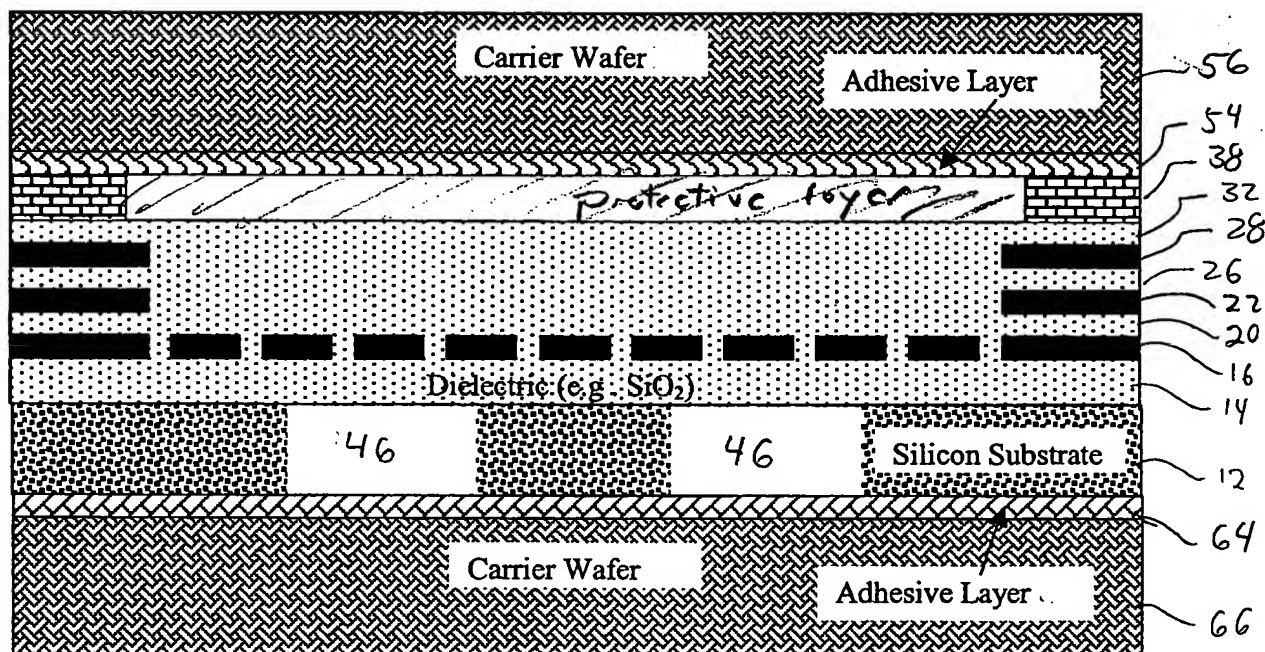


FIG. 36

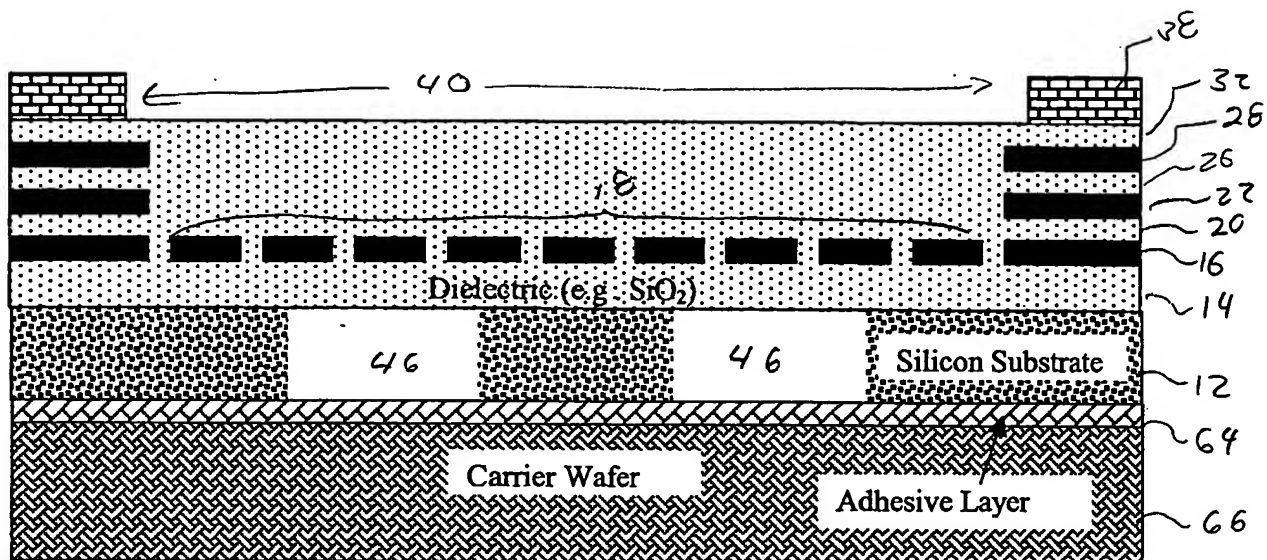


FIG. 37

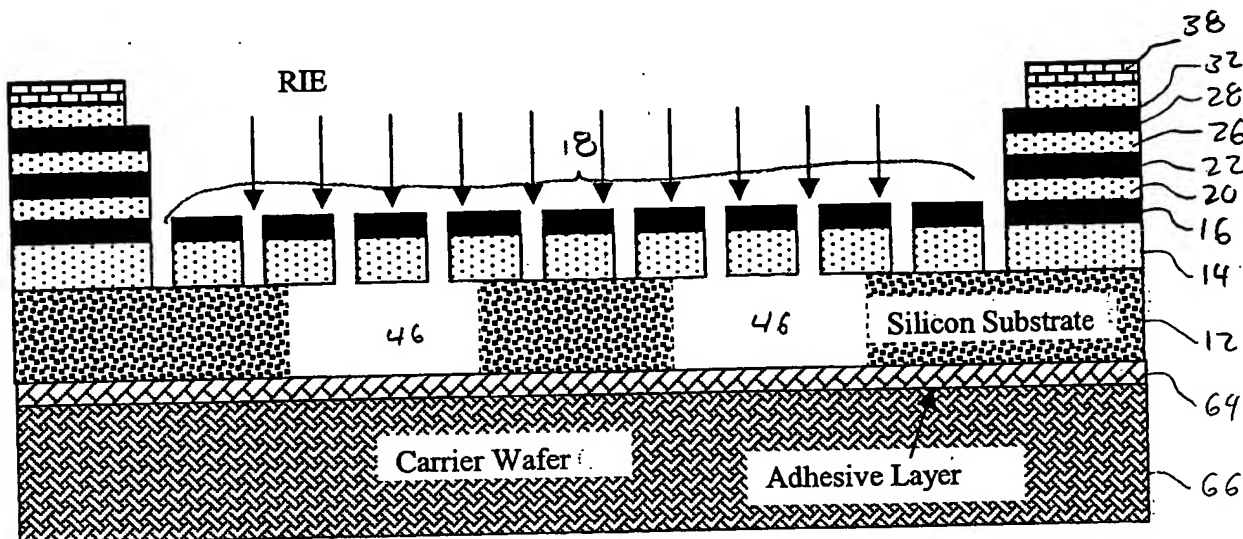


FIG. 38

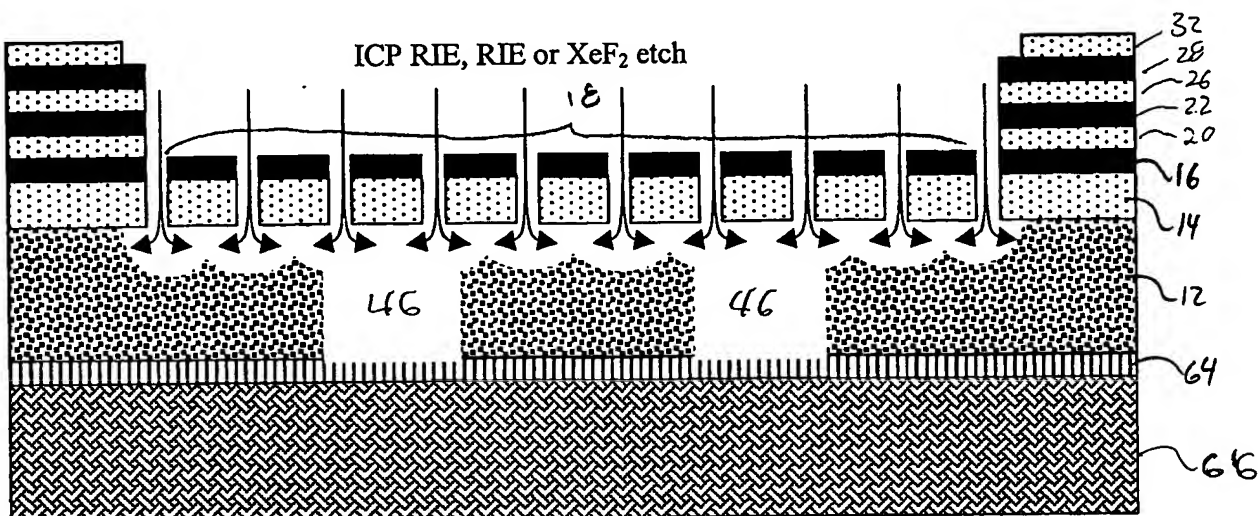


FIG. 39

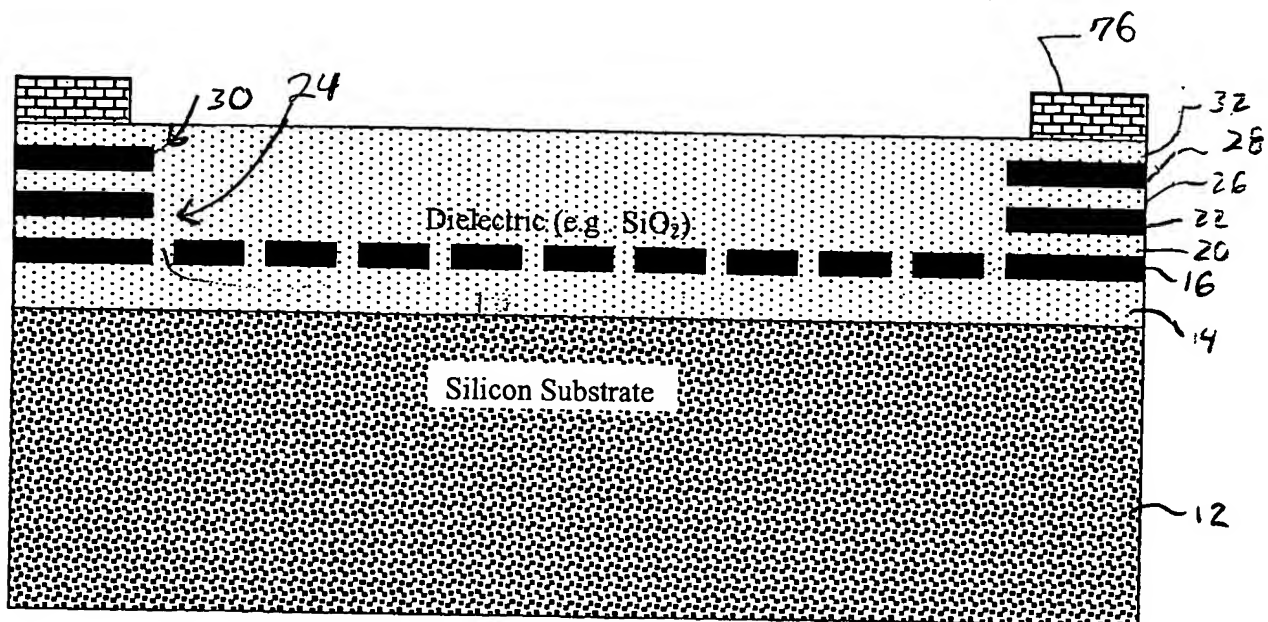


FIG. 40

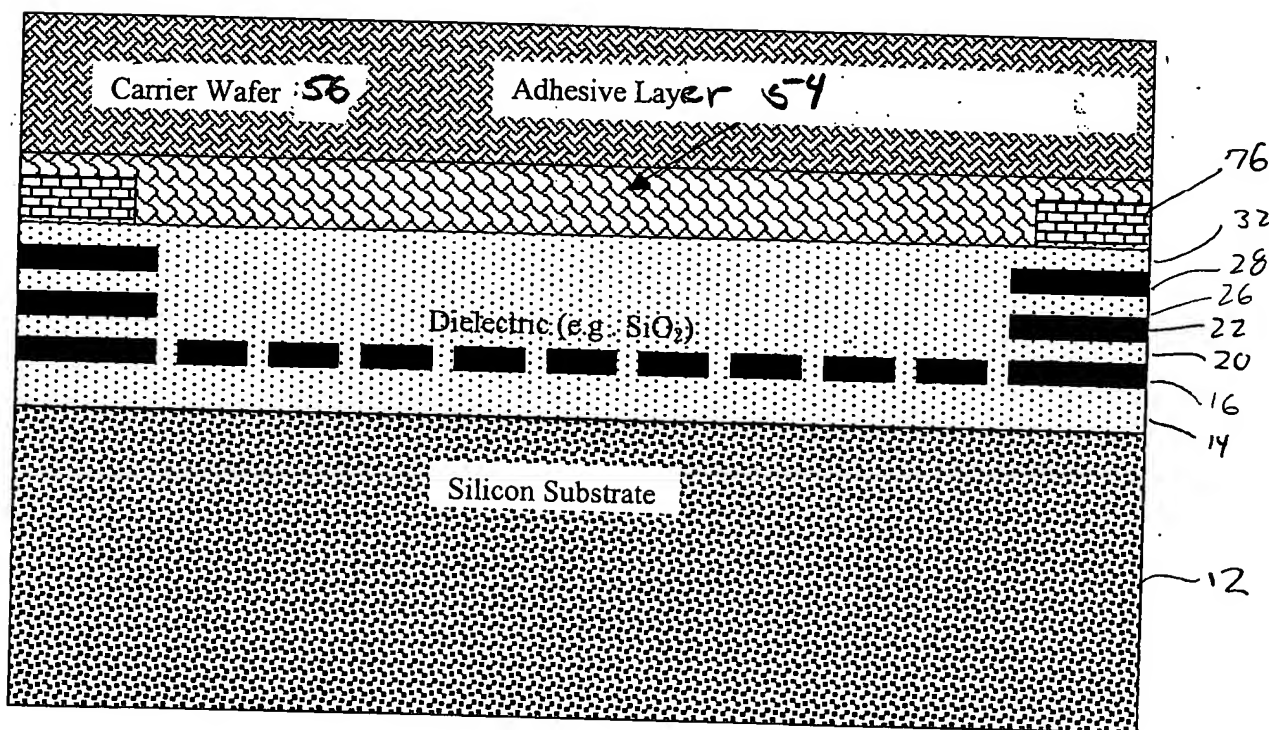




FIG. 43

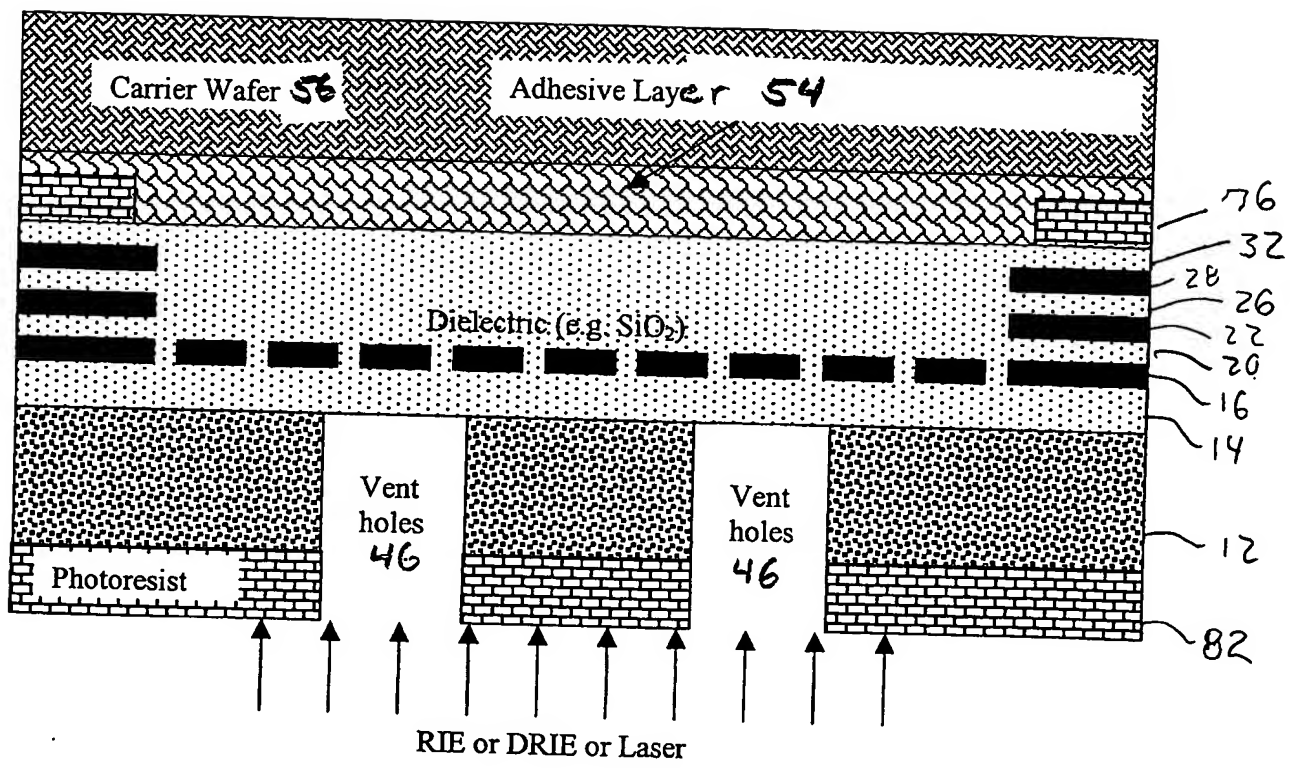
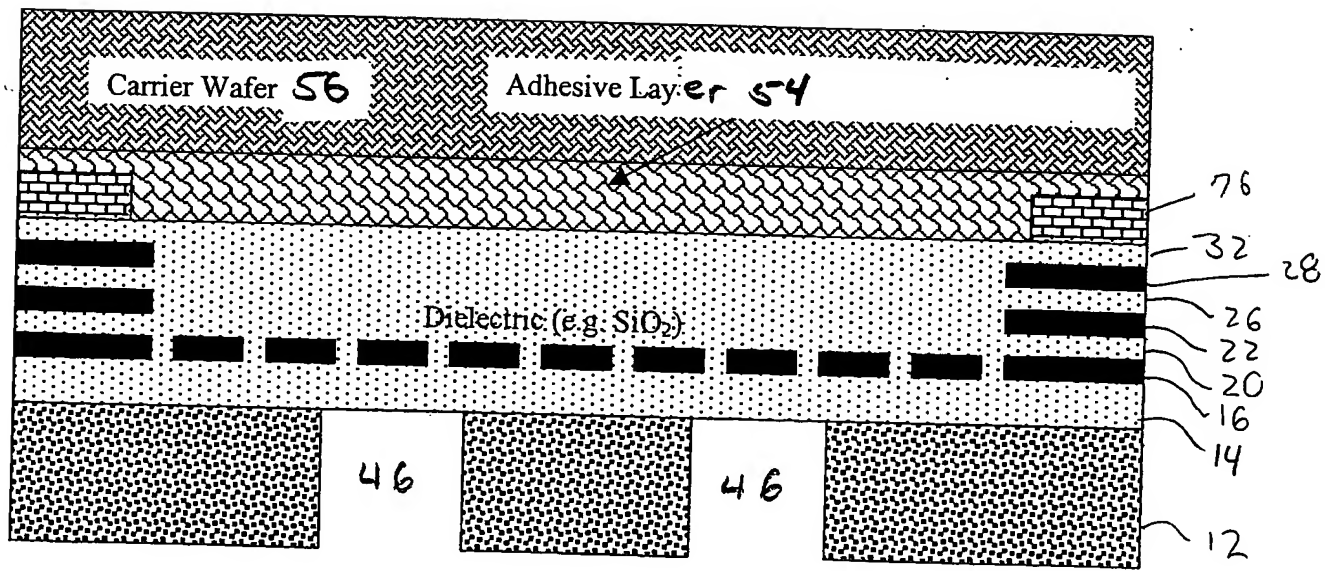


FIG. 44





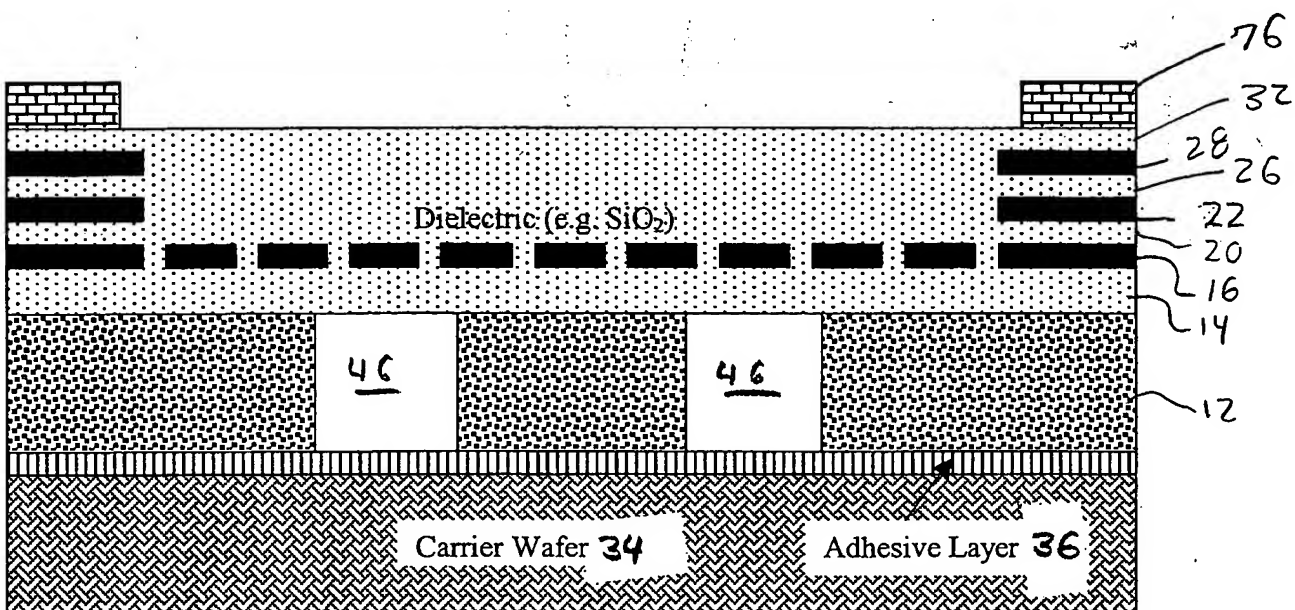
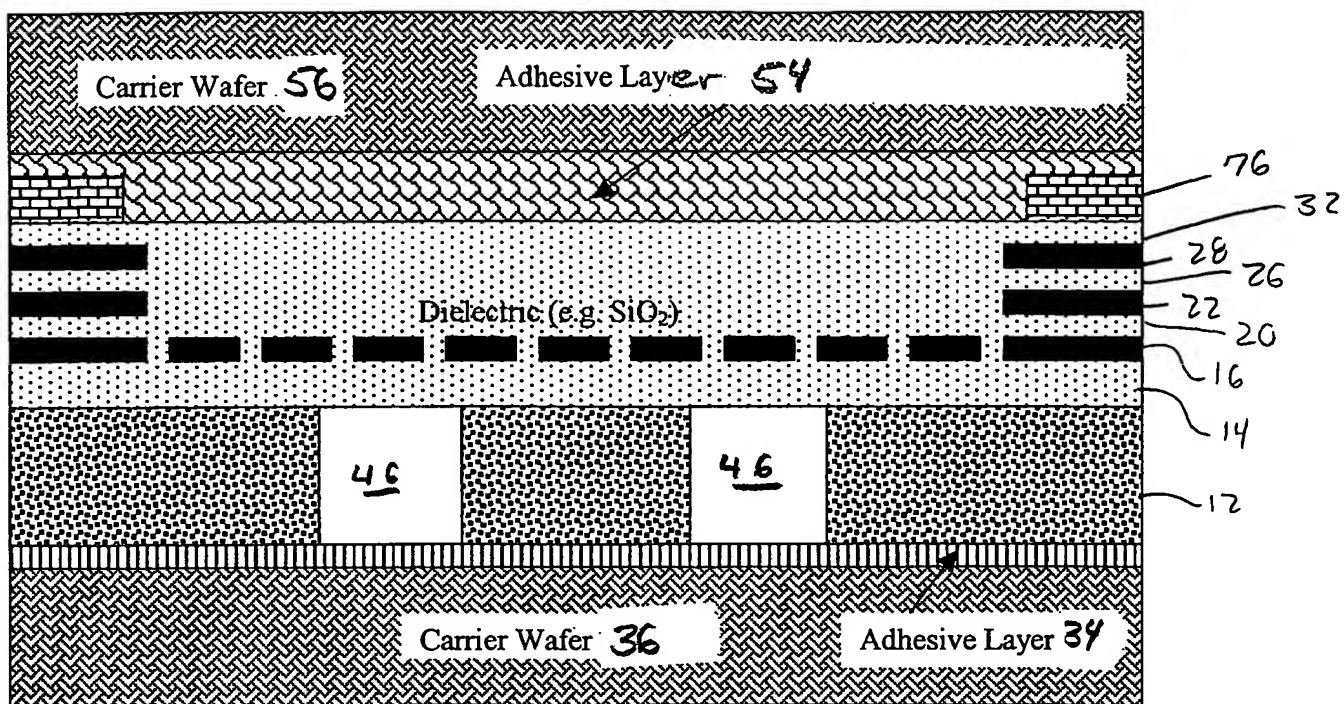




FIG. 47

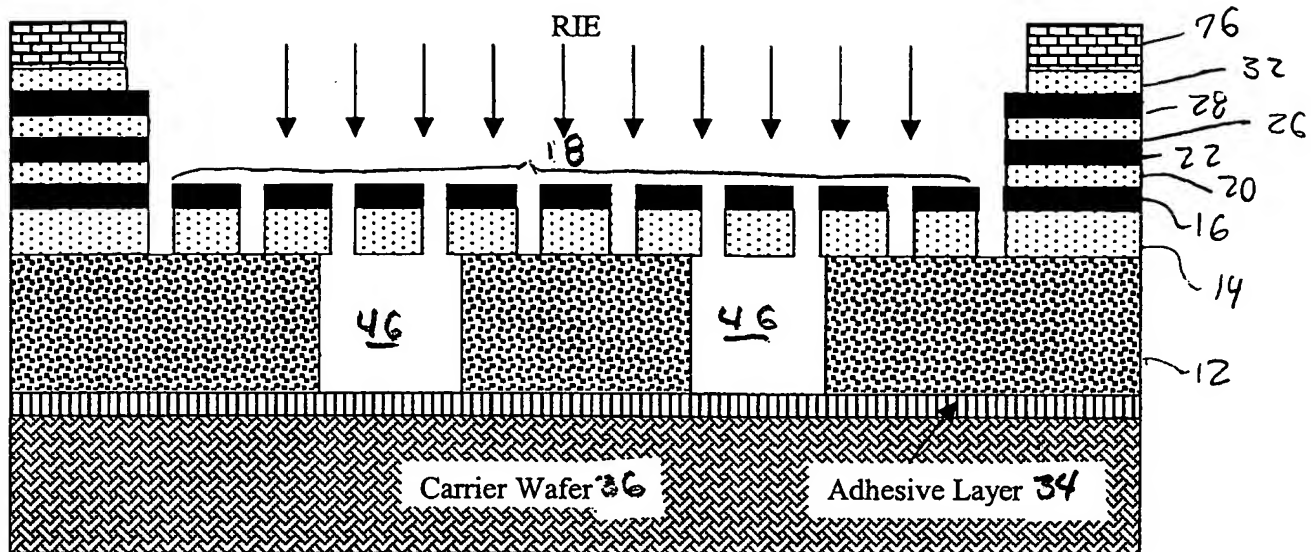


FIG. 48

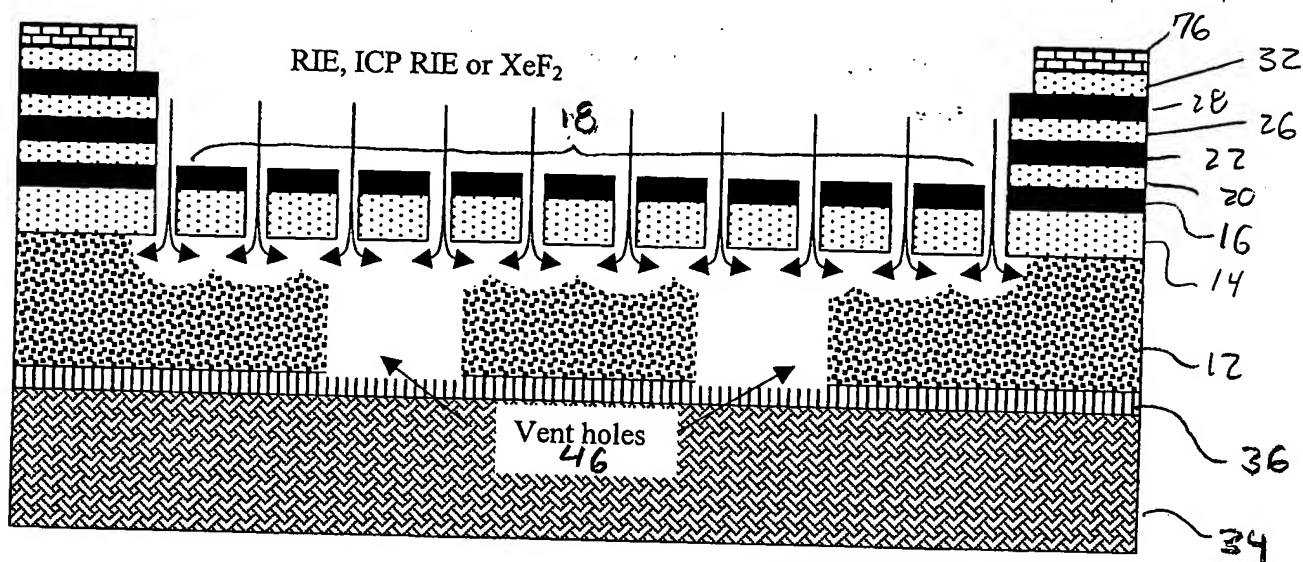


FIG. 49

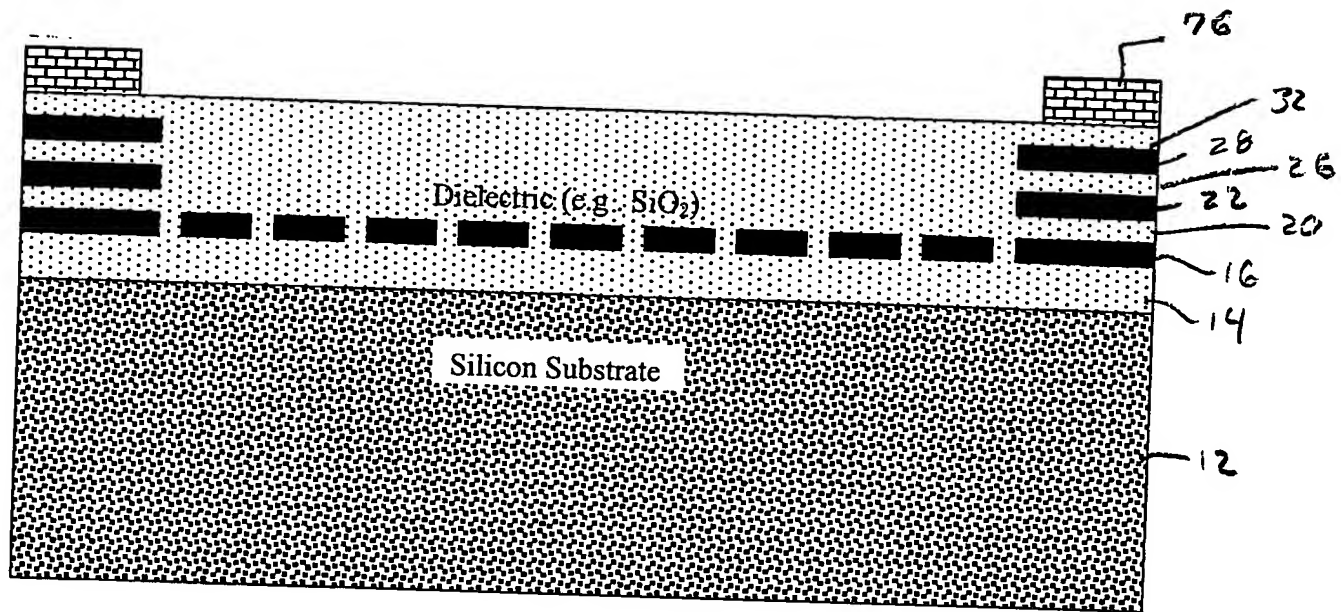


FIG. 50

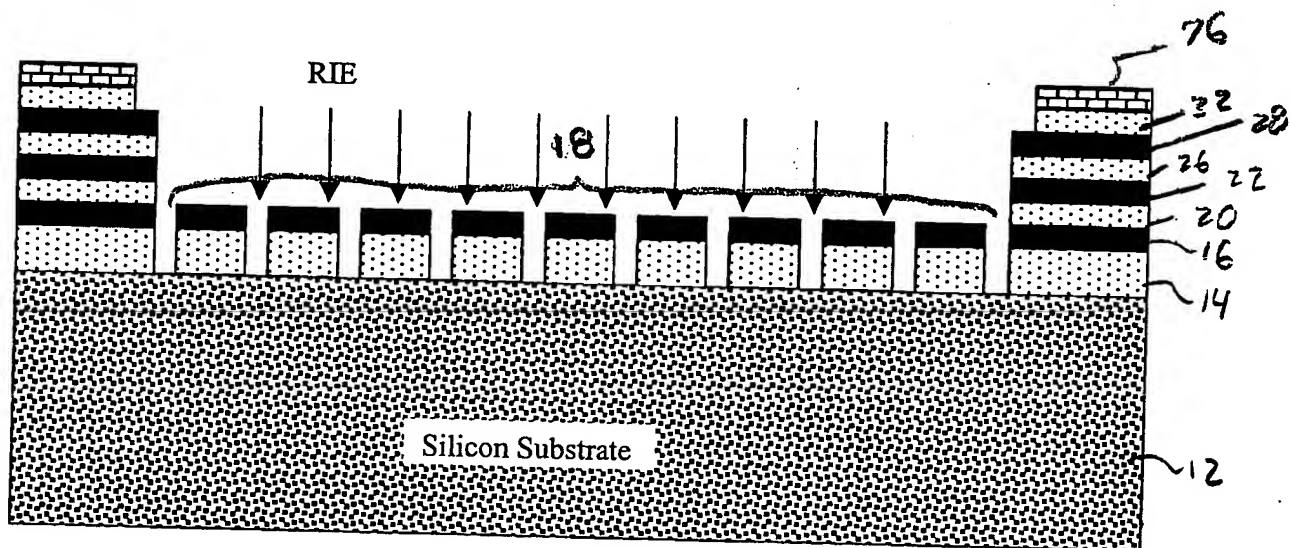


FIG. 51

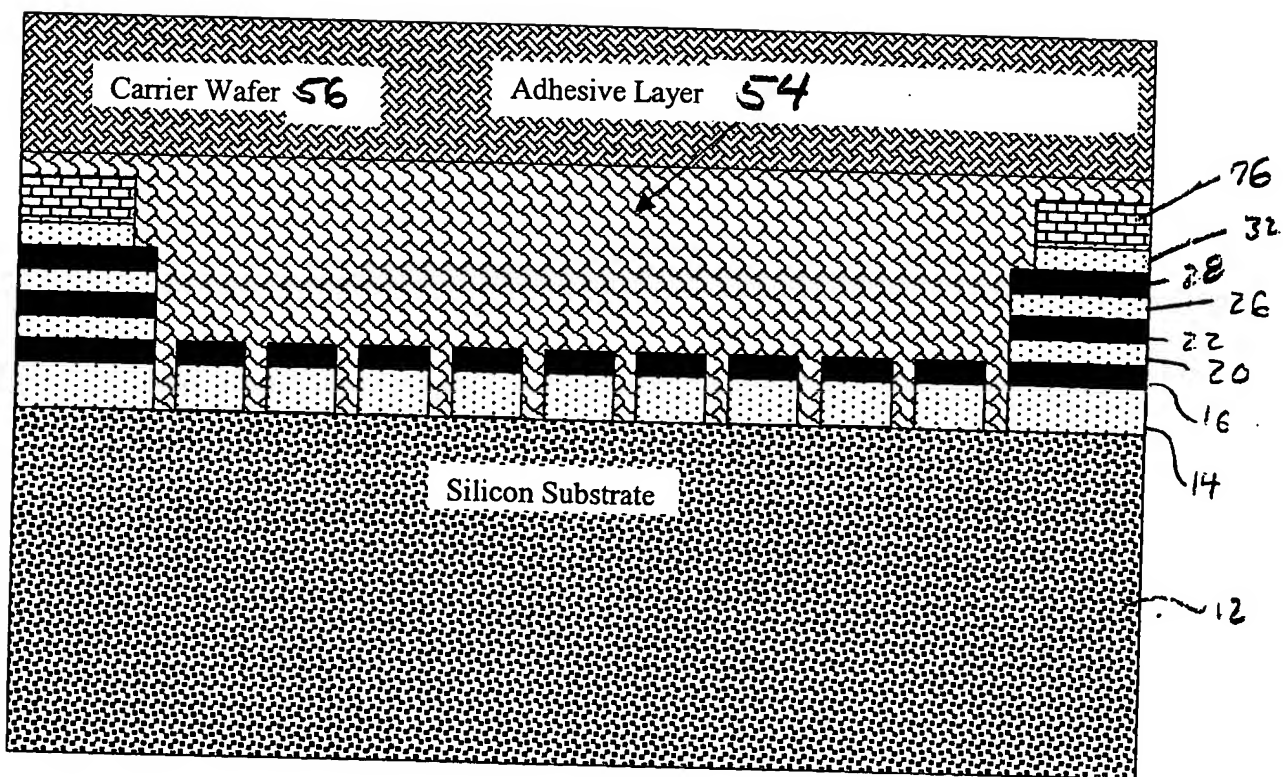


FIG. 52

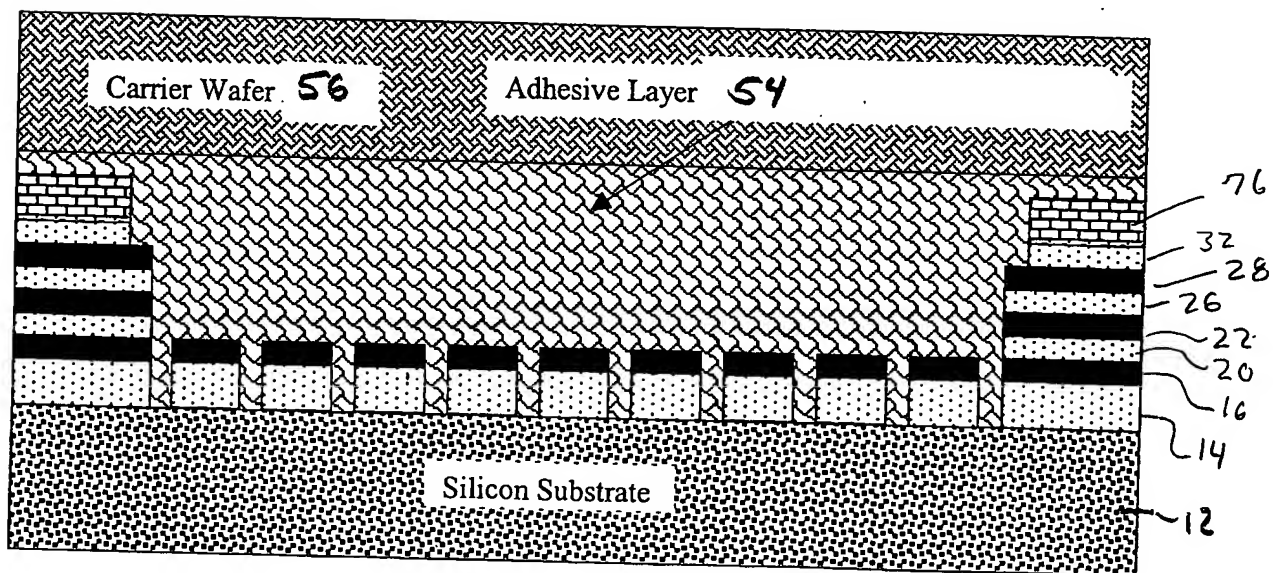


FIG. 53

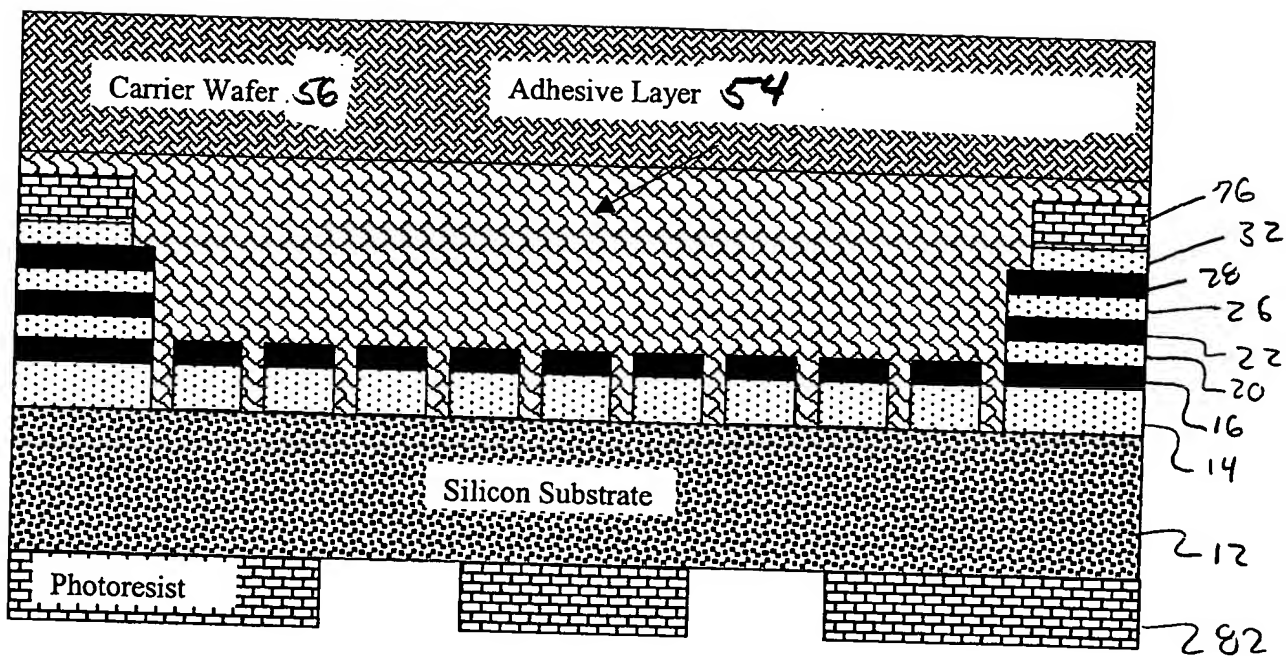


FIG. 54

